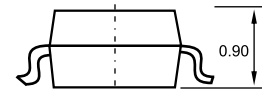
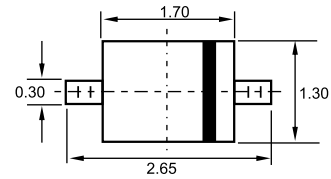


SOD-323



Dimensions in inches and (millimeters)

FEATURES

- Very low forward voltage
- High surge current
- Very small plastic SMD package.

APPLICATIONS

- Low voltage rectification
- High efficiency DC/DC conversion
- Voltage clamping
- Inverse polarity protection
- Low power consumption applications.

RELATED PRODUCTS

TYPE NUMBER	DESCRIPTION	FEATURE
PMEGxx05AEV	0.5 A; 20/30/40 V very low V_F MEGA Schottky rectifier	SOT666 package
PMEG2005EB	0.5 A; 20 V very low V_F MEGA Schottky rectifier	smaller SOD523 (SC-79) package
PMEG2010EA	1 A; 20 V very low V_F MEGA Schottky rectifier	higher forward current

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage				
	PMEG2005AEA		–	20	V
	PMEG3005AEA		–	30	V
	PMEG4005AEA		–	40	V
I_F	continuous forward current	note 1	–	0.5	A
I_{FRM}	repetitive peak forward current	$t_p \leq 1$ ms; $\delta \leq 0.5$	–	3.5	A
I_{FSM}	non-repetitive peak forward current	$t_p = 8$ ms; square wave	–	10	A
T_j	junction temperature	note 2	–	150	°C
T_{amb}	operating ambient temperature	note 2	–65	+150	°C
T_{stg}	storage temperature		–65	+150	°C

Notes

- Refer to SOD323 (SC-76) standard mounting conditions.
- For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; notes 1 and 2	450	K/W
		in free air; notes 2 and 3	210	K/W
R _{th j-s}	thermal resistance from junction to soldering point	note 4	90	K/W

Notes

1. Refer to SOD323 (SC-76) standard mounting conditions.
2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determination of the reverse power losses P_R and I_{F(AV)} rating will be available on request.
3. Device mounted on an FR4 printed-circuit board with copper clad 10 × 10 mm.
4. Solder point of cathode tab.

ELECTRICAL CHARACTERISTICS

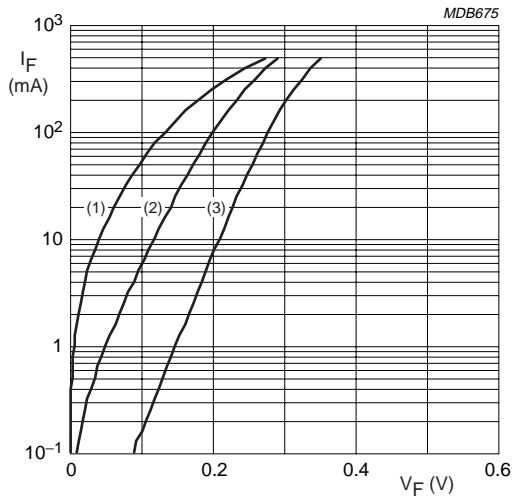
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	PMEG2005AEA		PMEG3005AEA		PMEG4005AEA		UNIT
			TYP.	MAX.	TYP.	MAX.	TYP.	MAX.	
V _F	forward voltage	I _F = 0.1 mA	90	130	90	130	95	130	mV
		I _F = 1 mA	150	190	150	200	155	210	mV
		I _F = 10 mA	210	240	215	250	220	270	mV
		I _F = 100 mA	280	330	285	340	295	350	mV
		I _F = 500 mA	355	390	380	430	420	470	mV
I _R	continuous reverse current	V _R = 10 V; note 1	15	40	12	30	7	20	μA
		V _R = 20 V; note 1	40	200	–	–	–	–	μA
		V _R = 30 V; note 1	–	–	40	150	–	–	μA
		V _R = 40 V; note 1	–	–	–	–	30	100	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz	66	80	55	70	43	50	pF

Note

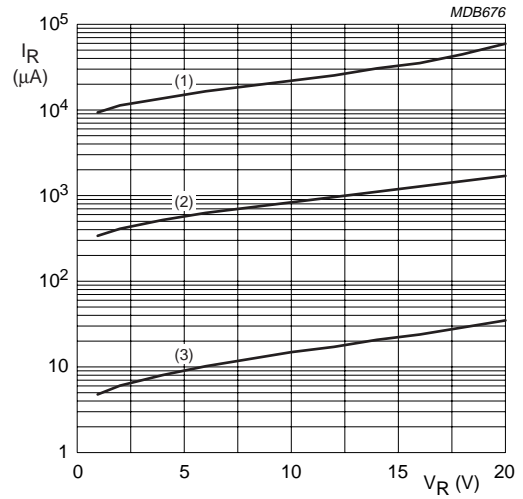
1. Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.

GRAPHICAL DATA



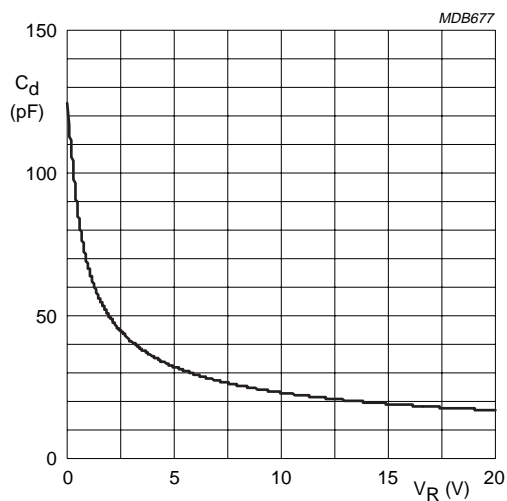
PMEG2005AEA
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.2 Forward current as a function of forward voltage; typical values.



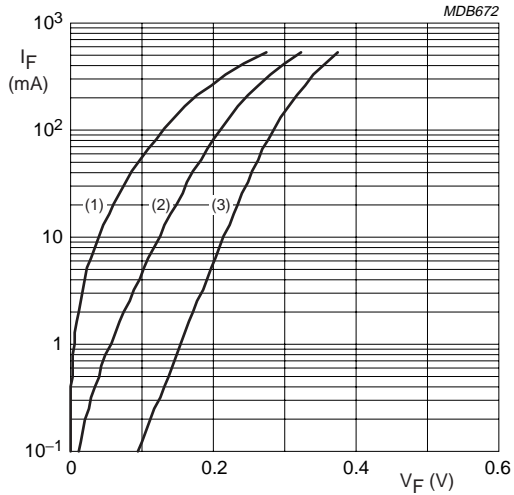
PMEG2005AEA
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



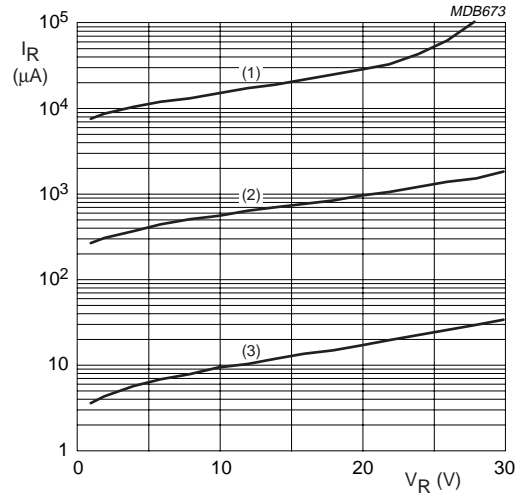
PMEG2005AEA
 $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.



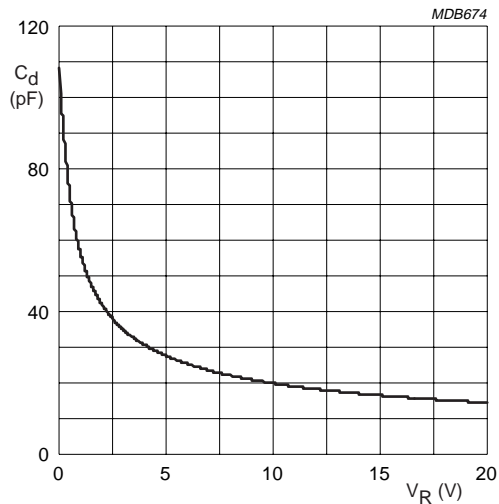
PMEG3005AEA
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.5 Forward current as a function of forward voltage; typical values.



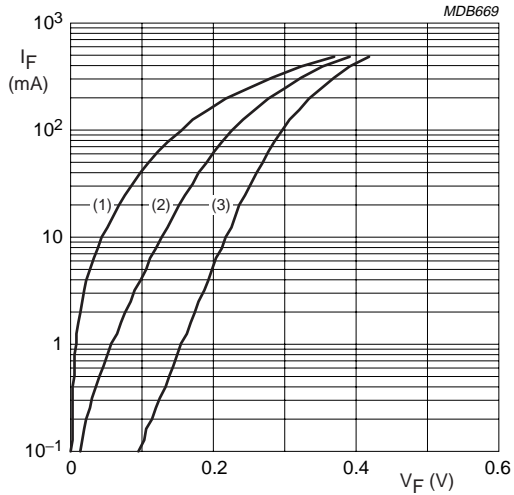
PMEG3005AEA
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
(2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
(3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.6 Reverse current as a function of reverse voltage; typical values.



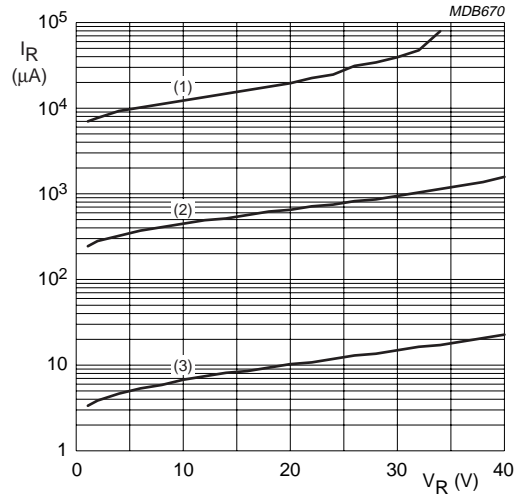
PMEG3005AEA
 $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.7 Diode capacitance as a function of reverse voltage; typical values.



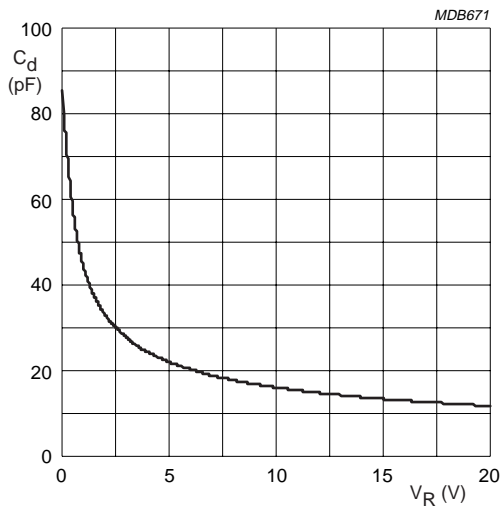
PMEG4005AEA
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.8 Forward current as a function of forward voltage; typical values.



PMEG4005AEA
 (1) $T_{amb} = 150\text{ }^{\circ}\text{C}$.
 (2) $T_{amb} = 85\text{ }^{\circ}\text{C}$.
 (3) $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.9 Reverse current as a function of reverse voltage; typical values.



PMEG4005AEA
 $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig.10 Diode capacitance as a function of reverse voltage; typical values.